

MOS FIELD EFFECT TRANSISTOR **2SJ601**

SWITCHING P-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION			ORDERING INFORMATION			
The 2SJ601 is P-channel MOS Field Effect Transistor designed			PART NUMBER		PACKAGE	
for solenoid, motor and lamp driver.			2SJ	601	TO-251	
FEATURES			2SJ6	01-Z	TO-252	
Low on-state resistance:						
$R_{DS(on)1} = 31 \text{ m}\Omega \text{ MAX.} (V_{GS} = -10 \text{ V}, \text{ In})$	ο = _18 Δ)					
$R_{DS(on)2} = 46 \text{ m}\Omega \text{ MAX.} (V_{GS} = -4.0 \text{ V}, \text{ m})$						
 Low Ciss: Ciss = 3300 pF TYP. 	10 - 10 M					
Built-in gate protection diode						
 TO-251/TO-252 package 				-		
• 10 201/10 202 package			2. 42	15- I''		
ABSOLUTE MAXIMUM RATINGS (1	「 _A = 25°C)		y on Con	C1.	(TO-251)	
Drain to Source Voltage ($V_{GS} = 0 V$)	Vdss	<u>-6</u> 0	V			
Gate to Source Voltage (Vgs = 0 V)	Vgss	∓20	V			
Drain Current (DC) (Tc = 25°C)	D(DC)	∓36	А			
Drain Current (pulse) Note1	D(pulse)	∓12 0	А			
Total Power Dissipation (Tc = 25°C)	Рт	65	W			
Total Power Dissipation ($T_A = 25^{\circ}C$)	Ρτ	1.0	W		(TO-252)	
Channel Temperature	Tch	150	°C			
Storage Temperature	Tstg	–55 to +150	°C			
Single Avalanche Current Note2	las	-35	А			
Single Avalanche Energy Note2	Eas	123	mJ		Ø	

Notes 1. PW \leq 10 μ s, Duty cycle \leq 1%

2. Starting T_{ch} = 25°C, R_G = 25 Ω , V_{GS} = -20 V \rightarrow 0 V

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

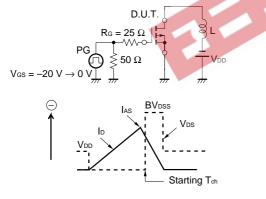
Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Zero Gate Voltage Drain Current	loss	$V_{DS} = -60 V, V_{GS} = 0 V$			-10	μA
Gate Leakage Current	lgss	$V_{GS} = \mp 20 V$, $V_{DS} = 0 V$			∓10	μA
Gate Cut-off Voltage	VGS(off)	$V_{DS} = -10 V$, $I_D = -1 mA$	1.5	2.0	2.5	V
Forward Transfer Admittance	y _{fs}	$V_{DS} = -10 V$, $I_D = -18 A$	15	30		S
Drain to Source On-state Resistance	RDS(on)1	V _{GS} = -10 V, I _D = -18 A		25	31	mΩ
	RDS(on)2	$V_{GS} = -4.0 V$, $I_D = -18 A$		32	46	mΩ
Input Capacitance	Ciss	V _{DS} = -10 V		3300		pF
Output Capacitance	Coss	V _{GS} = 0 V		580		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		230		pF
Turn-on Delay Time	td(on)	$V_{DD} = -30 V$, $I_D = -18 A$		11		ns
Rise Time	tr	V _{GS(on)} = -10 V		12		ns
Turn-off Delay Time	$t_{d(off)}$	$R_G = 0 \Omega$		80		ns
Fall Time	tr			53		ns
Total Gate Charge	QG	V _{DD} = -48 V		63		nC
Gate to Source Charge	QGS	V _{GS} = -10 V		10		nC
Gate to Drain Charge	Qgd	ID = -36 A		16		nC
Body Diode Forward Voltage	VF(S-D)	IF = -36 A, VGS = 0 V		1.0		V
Reverse Recovery Time	trr	$I_{\rm D} = -36 \text{ A}$ $I_{\rm F} = -36 \text{ A}, \text{ V}_{\rm GS} = 0 \text{ V}$ $I_{\rm F} = -36 \text{ A}, \text{ V}_{\rm GS} = 0 \text{ V}$ $di/dt = -100 \text{ A}/1/\text{s}$		52		ns
Reverse Recovery Charge	Qrr	di/dt = $-100 \text{ A}/\mu \text{s}$		108		nC



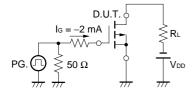
TEST CIRCUIT 2 SWITCHING TIME

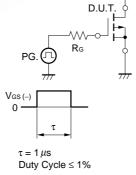
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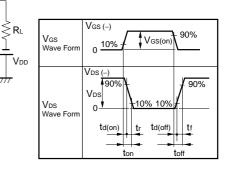
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TEST CIRCUIT 3 GATE CHARGE



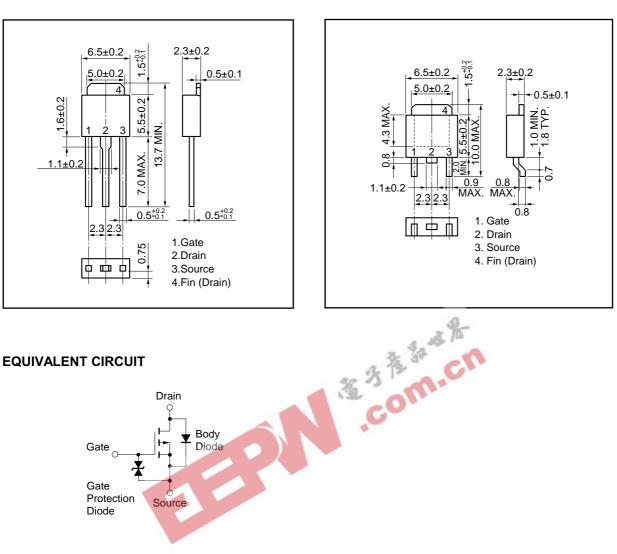




Preliminary Data Sheet D14646EJ1V0DS

PACKAGE DRAWINGS (Unit : mm)

1) TO-251 (MP-3)



2) TO-252 (MP-3Z)

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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